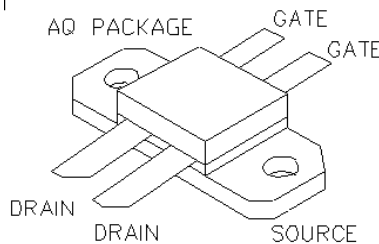




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features gold metal for greatly extended lifetime. Low output capacitance and high F_t enhance broadband performance



PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR

40Watts Push - Pull

Package Style AQ

HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
100Watts	1.5 °C/W	200 °C	-65°C to 150°C	4 A	70 V	70V	30V

RF CHARACTERISTICS (40WATTS OUTPUT)

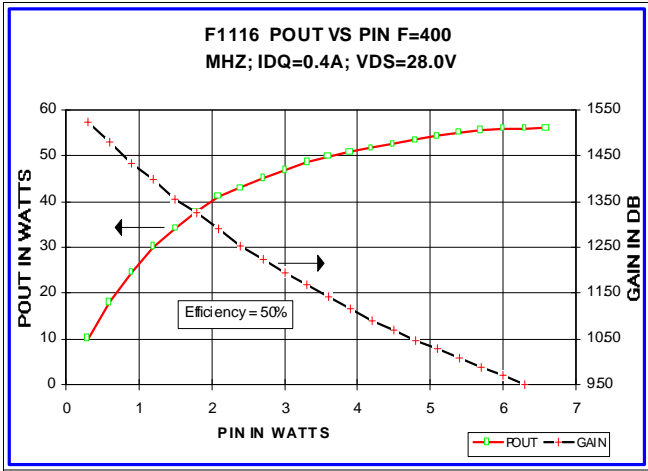
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	11			dB	$I_{dq} = 0.4 A, V_{ds} = 28.0V, F = 400 MHz$
η	Drain Efficiency		55		%	$I_{dq} = 0.4 A, V_{ds} = 28.0V, F = 400 MHz$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 0.4 A, V_{ds} = 28.0V, F = 400 MHz$

ELECTRICAL CHARACTERISTICS (EACH SIDE)

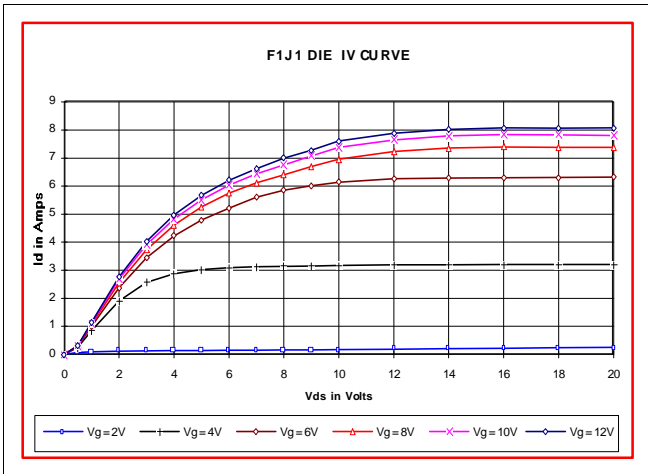
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	$I_{ds} = 0.05 A, V_{gs} = 0V$
Idss	Zero Bias Drain Current			1	mA	$V_{ds} = 28.0V, V_{gs} = 0V$
Igss	Gate Leakage Current			1	uA	$V_{ds} = 0V, V_{gs} = 30V$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.1 A, V_{gs} = V_{ds}$
gM	Forward Transconductance		1		Mho	$V_{ds} = 10V, V_{gs} = 5V$
Rdson	Saturation Resistance		1		Ohm	$V_{gs} = 20V, I_{ds} = 4A$
Idsat	Saturation Current		6		Amp	$V_{gs} = 20V, V_{ds} = 10V$
Ciss	Common Source Input Capacitance		40		pF	$V_{ds} = 28.0V, V_{gs} = 0V, F = 1 MHz$
Crss	Common Source Feedback Capacitance		5		pF	$V_{ds} = 28.0V, V_{gs} = 0V, F = 1 MHz$
Coss	Common Source Output Capacitance		30		pF	$V_{ds} = 28.0V, V_{gs} = 0V, F = 1 MHz$

F1116

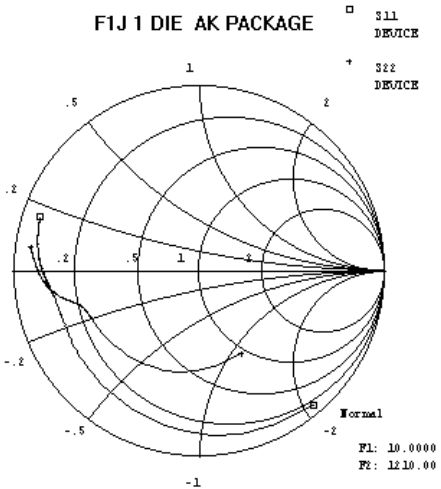
POUT VS PIN GRAPH



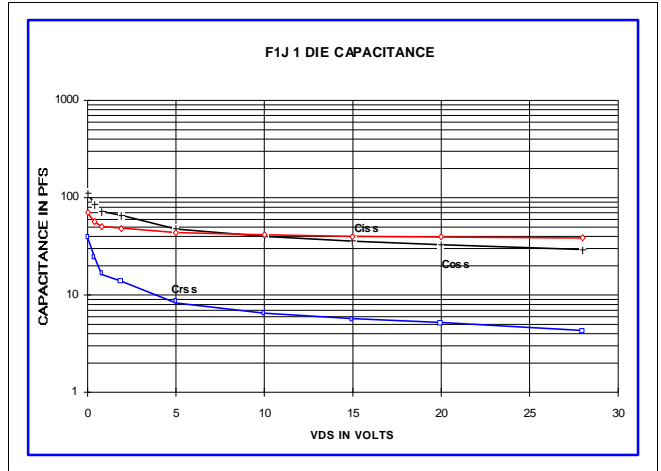
IV CURVE



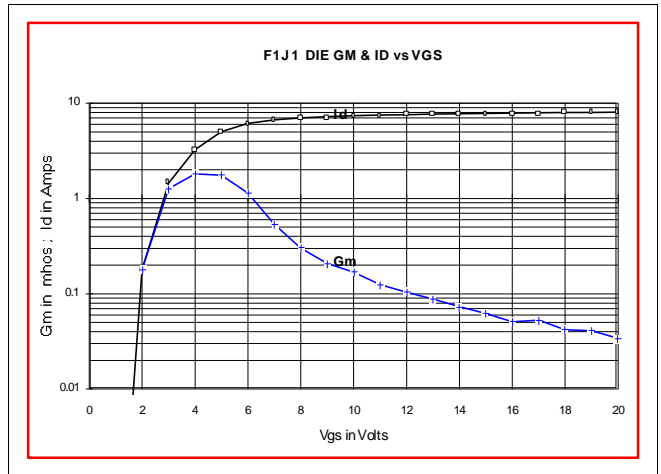
S11 AND S22 SMITH CHART



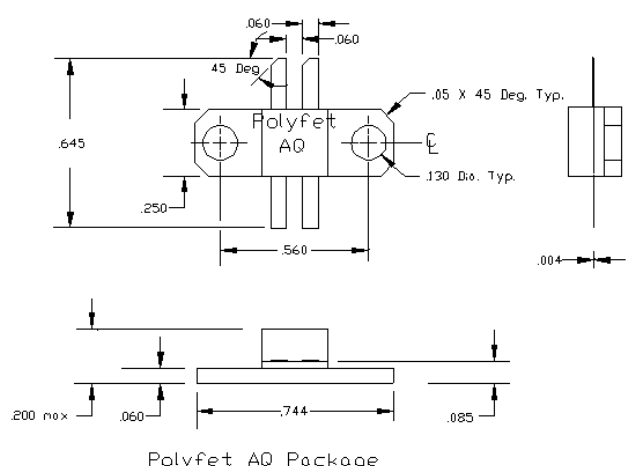
CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



PACKAGE DIMENSIONS IN INCHES



Tolerance 0.XX +/- 0.01 0.XXX +/- 0.005 inches